

AMENDMENTS TO THE SPECIFICATION

Replace the paragraph beginning at page 4, line 11 with:

For example, the gate insulating film 4 (total physical film thickness of 3.6 nm), composed of the first insulating film 16 of an EOT of 0.7 nm (physical film thickness of 0.7 nm) and the second insulating film 18 of an EOT of 0.8 nm (physical film thickness of 2.9 nm, assuming the dielectric constant of 14), has an EOT of 1.5 nm, and satisfies the equation, ~~EOT~~ $EOT \leq 1.5$ nm. Since the first insulating film 16 and the second insulating film 18 can sufficiently secure the physical thickness, tunnel leak current can be depressed.